ON Semiconductor

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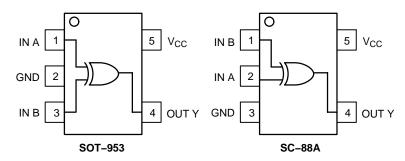
Single 2-Input XOR Gate

The NL17SG86 MiniGate[™] is an advanced high-speed CMOS 2-State XOR gate in ultra-small footprint.

The NL17SG86 input structures provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 2.7$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5 \mu A$ (Max) at $T_A = 25^{\circ}C$
- 4.6 V Overvoltage Tolerant (OVT) Input Pins ($V_{CC} \ge 0.9 \text{ V}$)
- Ultra-Small Packages
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



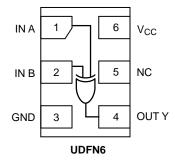


Figure 1. Pinouts (Top View)

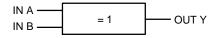
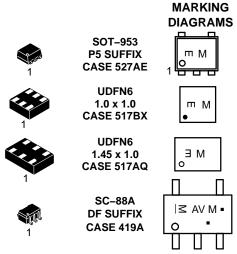


Figure 2. Logic Symbol



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E = Specific Device Code (E with 90 degree clockwise rotation)

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT						
	SOT-953	SC-88A	UDFN6			
1	IN A	IN B	IN A			
2	GND	IN A	IN B			
3	IN B	GND	GND			
4	OUT Y	OUT Y	OUT Y			
5	V _{CC}	V _{CC}	NC			
6			V _{CC}			

FUNCTION TABLE

A Input	OE Input	Y Output
L,	L	L
L	Н	н
н	L	н
Н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +5.5	V
V _{IN}	DC Input Voltage		-0.5 to +4.6	V
V _{OUT}	DC Output Voltage	Output at High or Low State ower–Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +4.6	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±20	mA
I _{CC}	DC Supply Current per Supply Pin		±20	mA
I _{GND}	DC Ground Current per Ground Pin		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V
I _{LATCHUP}	Latchup Performance Above V _{CC} and I	Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

Tested to EIA/JESD22-A114-A.

Tested to EIA/JESD22-A115-A.

- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0.0	3.6	V
V _{OUT}	Output Voltage Output at High or Low Power–Down Mode (V _{CC}	State = 0 V)	0.0 0.0	V _{CC} 3.6	V
T _A	Operating Temperature Range		- 55	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate $V_{CC} = 3.3 \text{ V} \pm$	0.3 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

							T _A =	$T_A = 25^{\circ}C$		$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$	
Symbol	Parameter	С	onditions	V _{CC} (V)	Min	Max	Min	Max	Unit		
V _{IH} High–Level				0.9	V _{CC}		V _{CC}		V		
	Input Voltage			1.1 to 1.3	0.7xV _{CC}		0.7xV _{CC}				
				1.4 to 1.6	0.65xV _{CC}		0.65xV _{CC}				
				1.65 to 1.95	0.65xV _{CC}		0.65xV _{CC}				
				2.3 to 2.7	1.7		1.7				
				3.0 to 3.6	2.0		2.0				
V _{IL}	Low-Level Input			0.9		GND		GND	V		
	Voltage			1.1 to 1.3		0.3xV _{CC}		0.3xV _{CC}			
				1.4 to 1.6		0.35xV _{CC}		0.35xV _{CC}			
				1.65 to 1.95		0.35xV _{CC}		0.35xV _{CC}			
				2.3 to 2.7		0.7		0.7			
				3.0 to 3.6		0.8		0.8			
V _{OH}	High-Level	V _{IN} =	I _{OH} = -20 μA	0.9	0.75		0.75		V		
	Output Voltage	Output Voltage V _{IH} or V _{IL}	$I_{OH} = -0.3 \text{ mA}$	1.1 to 1.3	0.75xV _{CC}		0.75xV _{CC}				
			$I_{OH} = -1.7 \text{ mA}$	1.4 to 1.6	0.75xV _{CC}		0.75xV _{CC}				
			$I_{OH} = -3.0 \text{ mA}$	1.65 to 1.95	V _{CC} -0.45		V _{CC} -0.4 5				
			$I_{OH} = -4.0 \text{ mA}$	2.3 to 2.7	2.0		2.0				
			$I_{OH} = -8.0 \text{ mA}$	3.0 to 3.6	2.48		2.48				
V_{OL}	Low-Level	V _{IN} =	I _{OL} = 20 μA	0.9		0.1		0.1	V		
	Output Voltage V _{IH} or V _{IL}	I _{OL} = 0.3 mA	1.1 to 1.3		0.25xV _{CC}		0.25xV _{CC}				
			I _{OL} = 1.7 mA	1.4 to 1.6		0.25xV _{CC}		0.25xV _{CC}			
			I _{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45			
			I _{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4			
			I _{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4			
I _{IN}	Input Leakage Current	0 ≤	V _{IN} ≤ 3.6 V	0 to 3.6		±0.1		±1.0	μΑ		
I _{CC}	Quiescent Supply Current	V _{IN} =	V _{CC} or GND	3.6		0.5		10.0	μΑ		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

Symbol Parameter		Parameter Test Condition V _{CC} (V)			$T_A = 25^{\circ}C$			$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$	
				Min	Тур	Max	Min	Max	
t _{PLH} ,	Propagation Delay,	C _L = 10 pF,	0.9	_	23	_	-	-	ns
t _{PHL}	A or B to Y	$R_L = 1 M\Omega$	1.1 to 1.3	-	11.7	20.9	-	39.1	
			1.4 to 1.6	-	6.7	10.0	-	11.8	
			1.65 to 1.95	_	5.1	6.6	-	7.6	
			2.3 to 2.7	_	3.4	4.1	-	4.7	
			3.0 to 3.6	_	2.7	3.3	-	3.9	
		C _L = 15 pF,	0.9	_	23.7	_	-	-	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	_	11.9	22.8	-	39.4	
			1.4 to 1.6	-	6.7	9.9	-	11.9	
			1.65 to 1.95	-	5.1	7.3	-	7.5	
			2.3 to 2.7	-	3.4	4.7	-	5.3	
			3.0 to 3.6	-	2.7	3.6	-	4.1	
		C _L = 30 pF,	0.9	-	32.1	-	-	-	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	-	15.7	31.4	-	59.4	
			1.4 to 1.6	-	8.7	13.9	-	16.9	
			1.65 to 1.95	-	6.5	9.8	-	10.2	
			2.3 to 2.7	_	4.2	6.0	-	6.5	
			3.0 to 3.6	-	3.4	4.7	-	5.1	
C _{IN}	Input Capacitance		0 to 3.6		3	-	-	-	pF
C _O	Output Capacitance	V _O = GND	0		3	-	-	-	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	_	_	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. CPD is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. CPD is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

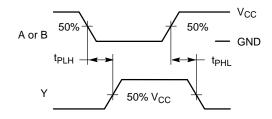
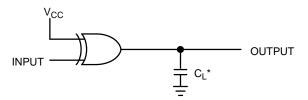


Figure 3. Switching Waveform



*Includes all probe and jig capacitance.
A 1 MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

ORDERING INFORMATION

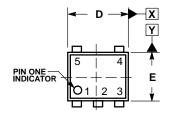
Device	Package	Shipping [†]
NL17SG86P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel
NL17SG86DFT2G	SC-88A (Pb-Free)	3000 / Tape & Reel
NL17SG86AMUTCG*	UDFN6 1.45 x 1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG86CMUTCG*	UDFN6 1 x 1 mm (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

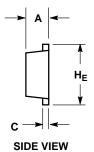
^{*}In Development.

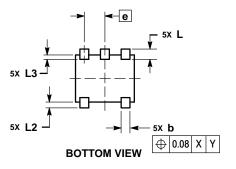
PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E



TOP VIEW

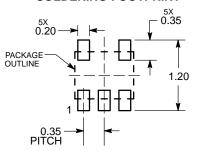




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

		MILLIMETERS				
L	DIM	MIN	NOM	MAX		
	Α	0.34	0.37	0.40		
L	b	0.10	0.15	0.20		
	С	0.07	0.12	0.17		
	D	0.95	1.00	1.05		
	Ε	0.75	0.80	0.85		
	е		0.35 BS	С		
F	HΕ	0.95	1.00	1.05		
	Г	0.175 REF				
	L2	0.05	0.10	0.15		
	L3			0.15		

SOLDERING FOOTPRINT*

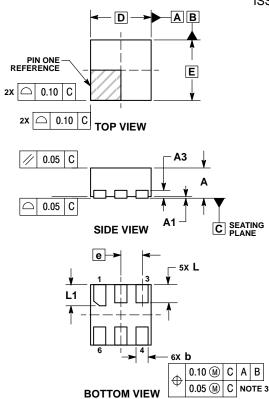


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

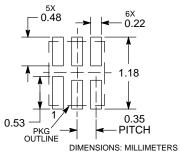
UDFN6, 1x1, 0.35P CASE 517BX ISSUE O



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
A3	0.13 REF				
b	0.12	0.22			
D	1.00	BSC			
Е	1.00	BSC			
е	0.35 BSC				
L	0.25	0.35			
L1	0.30	0.40			

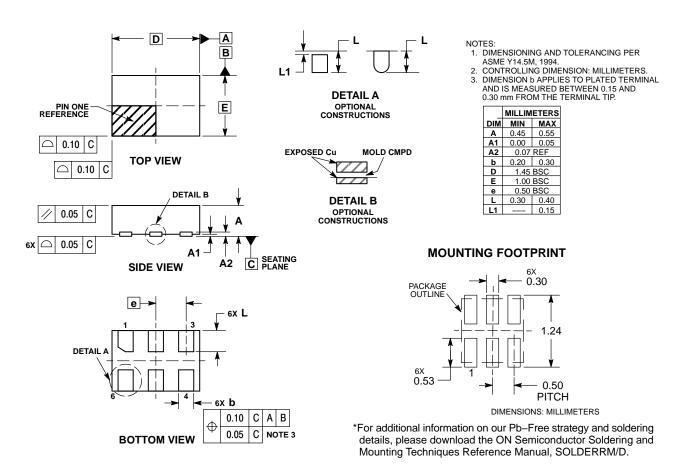
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5PCASE 517AQ ISSUE O



PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353)

CASE 419A-02 **ISSUE L**

NOTES:

BURRS.

DIM

В 0.045

AUTES.

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. 419A-01 OBSOLETE. NEW STANDARD

INCHES

MIN MAX

0.053

0.043

0.071 0.087

0.031

D 0.004 0.012

0.026 BSC 0.004 0.004 0.010

0.004 0.012

0.008 REF S 0.079 0.087

DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE

MILLIMETERS

MIN MAX

0.10 0.30

0.65 BSC

0.10 0.30 0.20 REF

2.20

1.35

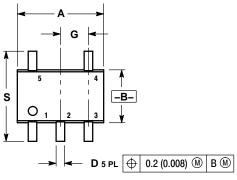
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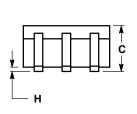
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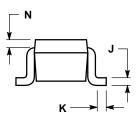
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0.80

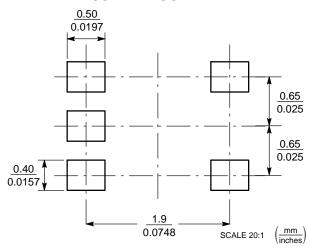
0.10 0.25







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NLX1G11AMUTCG NLX1G97MUTCG 74LS38 74LVC32ADTR2G MC74HCT20ADTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G
NLV74HC02ADR2G 74HC32S14-13 74LS133 74LVC1G32Z-7 M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7
NLV74HC08ADTR2G NLV74HC14ADR2G NLV74HC20ADR2G NLX2G86MUTCG 5962-8973601DA 74LVC2G02HD4-7
NLU1G00AMUTCG 74LVC2G32RA3-7 74LVC2G00HD4-7 NL17SG02P5T5G 74LVC2G00HK3-7 74LVC2G86HK3-7
NLX1G99DMUTWG NLVVHC1G00DFT2G NLVHC1G08DFT2G NLV7SZ57DFT2G NLV74VHC04DTR2G NLV27WZ86USG
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